

Title (en)
ESD protection thyristor with trigger diode

Title (de)
ESD-Schutzthyristor mit Triggerdiode

Title (fr)
Thyristor de protection ESD avec diode de déclenchement

Publication
EP 0982776 A2 20000301 (EN)

Application
EP 99306769 A 19990825

Priority
• JP 23917098 A 19980825
• JP 23095599 A 19990817

Abstract (en)
An electrostatic discharge protection device according to the present invention is provided at an input or an output of a semiconductor integrated circuit for protecting an internal circuit of the semiconductor integrated circuit from an electrostatic surge flowing into or out of the semiconductor integrated circuit. The electrostatic discharge protection device includes: a thyristor; and a trigger diode for triggering the thyristor with a low voltage. The trigger diode includes: an n-type cathode high impurity concentration region; a p-type anode high impurity concentration region; and an insulator section for electrically insulating a silicide layer formed on a surface of the n-type cathode high impurity concentration region from another silicide layer formed on a surface of the p-type anode high impurity concentration region. <IMAGE>

IPC 1-7
H01L 27/02; **H01L 29/74**

IPC 8 full level
H01L 21/332 (2006.01); **H01L 21/822** (2006.01); **H01L 21/8238** (2006.01); **H01L 27/02** (2006.01); **H01L 27/04** (2006.01); **H01L 27/092** (2006.01); **H01L 29/74** (2006.01); **H01L 29/866** (2006.01)

CPC (source: EP KR US)
H01L 27/0248 (2013.01 - EP US); **H01L 27/0259** (2013.01 - EP US); **H01L 27/0262** (2013.01 - EP US); **H01L 27/04** (2013.01 - KR); **H01L 29/7412** (2013.01 - EP US)

Cited by
CN103681651A; GB2368975A; GB2368975B; US6538266B2

Designated contracting state (EPC)
DE FR GB

DOCDB simple family (publication)
EP 0982776 A2 20000301; **EP 0982776 A3 20001102**; **EP 0982776 B1 20080416**; DE 69938523 D1 20080529; DE 69938523 T2 20090507; JP 2000138295 A 20000516; JP 4256544 B2 20090422; KR 100325553 B1 20020306; KR 20000017536 A 20000325; TW 441124 B 20010616; US 2002037621 A1 20020328; US 2002039825 A1 20020404; US 6338986 B1 20020115; US 6524893 B2 20030225; US 6696730 B2 20040224

DOCDB simple family (application)
EP 99306769 A 19990825; DE 69938523 T 19990825; JP 23095599 A 19990817; KR 19990035476 A 19990825; TW 88114562 A 19990825; US 210801 A 20011205; US 332101 A 20011206; US 37910899 A 19990823